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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

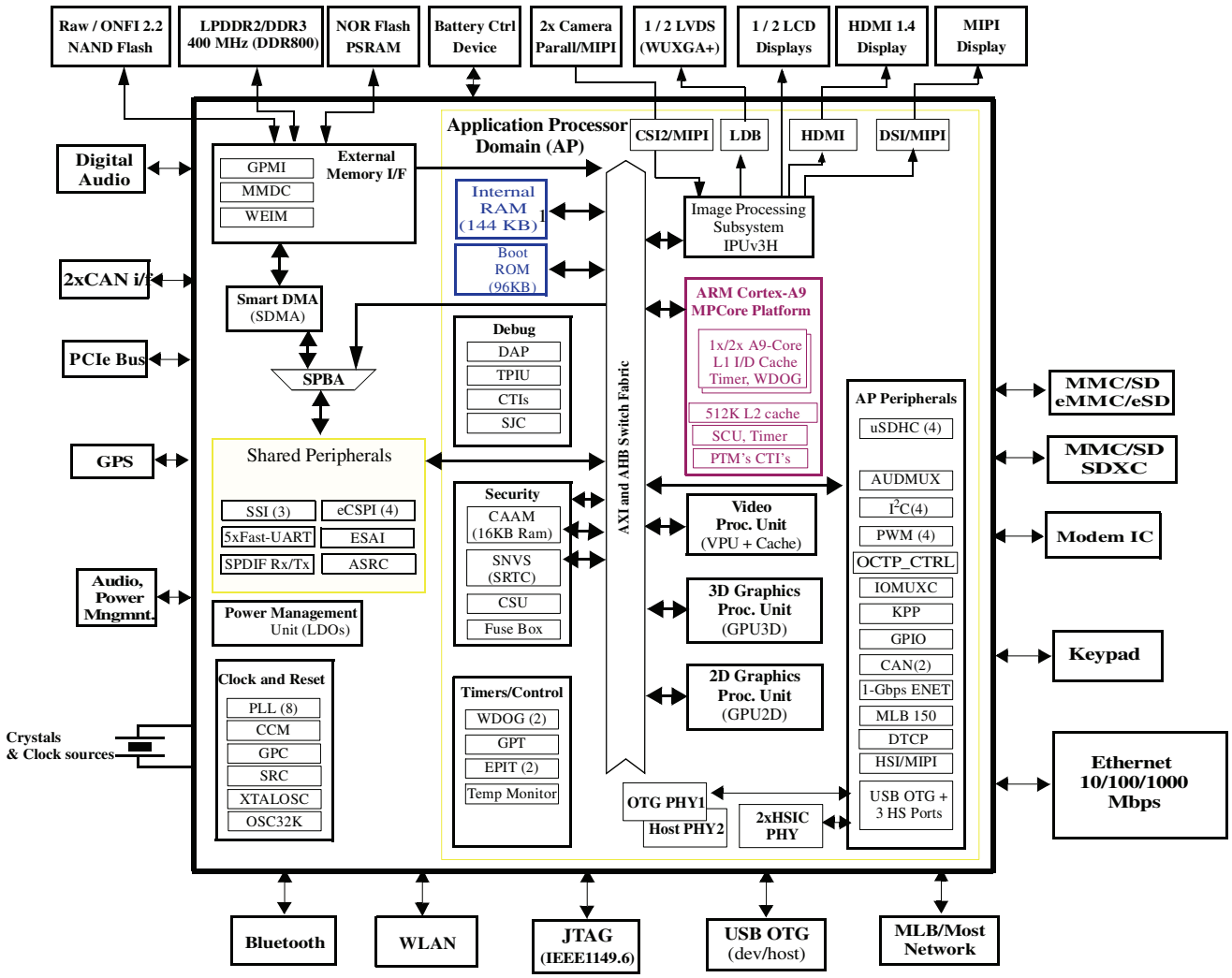
Details	
Product Status	Active
Core Processor	ARM® Cortex®-A9
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	800MHz
Co-Processors/DSP	Multimedia; NEON™ SIMD
RAM Controllers	LPDDR2, LVDDR3, DDR3
Graphics Acceleration	Yes
Display & Interface Controllers	Keypad, LCD
Ethernet	10/100/1000Mbps (1)
SATA	-
USB	USB 2.0 + PHY (4)
Voltage - I/O	1.8V, 2.5V, 2.8V, 3.3V
Operating Temperature	-40°C ~ 125°C (TJ)
Security Features	ARM TZ, Boot Security, Cryptography, RTIC, Secure Fusebox, Secure JTAG, Secure Memory, Secure RTC, Tamper Detection
Package / Case	624-LFBGA
Supplier Device Package	624-MAPBGA (21x21)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mcimx6s1avm08ab

2 Architectural Overview

The following subsections provide an architectural overview of the i.MX 6Solo/6DualLite processor system.

2.1 Block Diagram

Figure 2 shows the functional modules in the i.MX 6Solo/6DualLite processor system.



1 144 KB RAM including 16 KB RAM inside the CAAM.

2 For i.MX 6Solo, there is only one A9-core platform in the chip; for i.MX 6DualLite, there are two A9-core platforms.

Figure 2. i.MX 6Solo/6DualLite System Block Diagram

Table 2. i.MX 6Solo/6DualLite Modules List (continued)

Block Mnemonic	Block Name	Subsystem	Brief Description
uSDHC-1 uSDHC-2 uSDHC-3 uSDHC-4	SD/MMC and SDXC Enhanced Multi-Media Card / Secure Digital Host Controller	Connectivity Peripherals	i.MX 6Solo/6DualLite specific SoC characteristics: All four MMC/SD/SDIO controller IPs are identical and are based on the uSDHC IP. They are: • Fully compliant with MMC command/response sets and Physical Layer as defined in the Multimedia Card System Specification, v4.2/4.3/4.4 including high-capacity (size > 2 GB) cards HC MMC. • Fully compliant with SD command/response sets and Physical Layer as defined in the SD Memory Card Specifications, v3.0 including high-capacity SDHC cards up to 32 GB. • Fully compliant with SDIO command/response sets and interrupt/read-wait mode as defined in the SDIO Card Specification, Part E1, v3.0 All four ports support: • 1-bit or 4-bit transfer mode specifications for SD and SDIO cards up to UHS-I SDR104 mode (104 MB/s max) • 1-bit, 4-bit, or 8-bit transfer mode specifications for MMC cards up to 52 MHz in both SDR and DDR modes (104 MB/s max) However, the SoC level integration and I/O muxing logic restrict the functionality to the following: • Instances #1 and #2 are primarily intended to serve as external slots or interfaces to on-board SDIO devices. These ports are equipped with “Card detection” and “Write Protection” pads and do not support hardware reset. • Instances #3 and #4 are primarily intended to serve interfaces to embedded MMC memory or interfaces to on-board SDIO devices. These ports do not have “Card detection” and “Write Protection” pads and do support hardware reset. • All ports can work with 1.8 V and 3.3 V cards. There are two completely independent I/O power domains for Ports #1 and #2 in four bit configuration (SD interface). Port #3 is placed in his own independent power domain and port #4 shares power domain with some other interfaces.
FlexCAN-1 FlexCAN-2	Flexible Controller Area Network	Connectivity Peripherals	The CAN protocol was primarily, but not only, designed to be used as a vehicle serial data bus, meeting the specific requirements of this field: real-time processing, reliable operation in the Electromagnetic interference (EMI) environment of a vehicle, cost-effectiveness and required bandwidth. The FlexCAN module is a full implementation of the CAN protocol specification, Version 2.0 B, which supports both standard and extended message frames.

Table 7. Absolute Maximum Ratings (continued)

Parameter Description	Symbol	Min	Max	Unit
ESD damage immunity: • Human Body Model (HBM) • Charge Device Model (CDM)	V_{esd}	 — —	 2000 500	V
Storage temperature range	$T_{STORAGE}$	-40	150	°C

1 OVDD is the I/O supply voltage.

4.1.2 Thermal Resistance

4.1.2.1 BGA Case 2240 Package Thermal Resistance

Table 8 displays the thermal resistance data.

Table 8. Thermal Resistance Data

Rating	Test Conditions	Symbol	Value	Unit
Junction to Ambient[1]	Single-layer board (1s); natural convection[2] Four-layer board (2s2p); natural convection[2]	$R_{\theta JA}$ $R_{\theta JA}$	38 23	°C/W °C/W
Junction to Ambient[1]	Single-layer board (1s); airflow 200 ft/min[2,3] Four-layer board (2s2p); airflow 200 ft/min[2,3]	$R_{\theta JA}$ $R_{\theta JA}$	30 20	°C/W °C/W
Junction to Board[1,4]		$R_{\theta JB}$	14	°C/W
Junction to Case[1,5]		$R_{\theta JC}$	6	°C/W
Junction to Package Top[1,6]	Natural Convection	Ψ_{JT}	2	°C/W

1 Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.

2 Per JEDEC JESD51-2 with the single layer board horizontal. Thermal test board meets JEDEC specification for the specified package.

3 Per JEDEC JESD51-6 with the board horizontal.

4 Thermal resistance between the die and the printed circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.

5 Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).

6 Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.

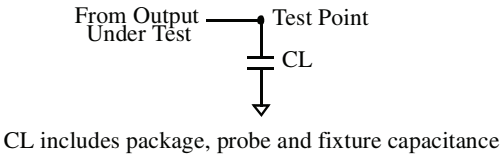


Figure 4. Load Circuit for Output

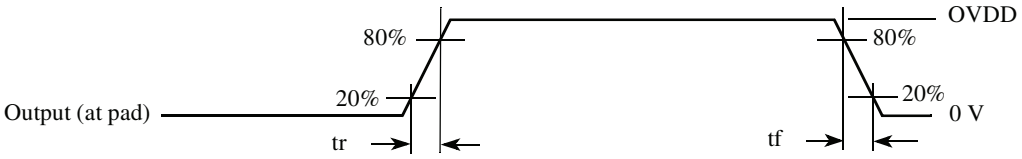


Figure 5. Output Transition Time Waveform

4.7.1 General Purpose I/O AC Parameters

The I/O AC parameters for GPIO in slow and fast modes are presented in the Table 29 and Table 30, respectively. Note that the fast or slow I/O behavior is determined by the appropriate control bits in the IOMUXC control registers.

Table 29. General Purpose I/O AC Parameters 1.8 V Mode

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Output Pad Transition Times, rise/fall (Max Drive, ipp_dse=111)	tr, tf	15 pF Cload, slow slew rate 15 pF Cload, fast slew rate	—	—	2.72/2.79 1.51/1.54	ns
Output Pad Transition Times, rise/fall (High Drive, ipp_dse=101)	tr, tf	15 pF Cload, slow slew rate 15 pF Cload, fast slew rate	—	—	3.20/3.36 1.96/2.07	
Output Pad Transition Times, rise/fall (Medium Drive, ipp_dse=100)	tr, tf	15 pF Cload, slow slew rate 15 pF Cload, fast slew rate	—	—	3.64/3.88 2.27/2.53	
Output Pad Transition Times, rise/fall (Low Drive. ipp_dse=011)	tr, tf	15 pF Cload, slow slew rate 15 pF Cload, fast slew rate	—	—	4.32/4.50 3.16/3.17	
Input Transition Times[1]	trm	—	—	—	25	ns

[1] Hysteresis mode is recommended for inputs with transition times greater than 25 ns.

Table 30. General Purpose I/O AC Parameters 3.3 V Mode

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Output Pad Transition Times, rise/fall (Max Drive, ipp_dse=101)	tr, tf	15 pF Cload, slow slew rate 15 pF Cload, fast slew rate	—	—	1.70/1.79 1.06/1.15	ns
Output Pad Transition Times, rise/fall (High Drive, ipp_dse=011)	tr, tf	15 pF Cload, slow slew rate 15 pF Cload, fast slew rate	—	—	2.35/2.43 1.74/1.77	
Output Pad Transition Times, rise/fall (Medium Drive, ipp_dse=010)	tr, tf	15 pF Cload, slow slew rate 15 pF Cload, fast slew rate	—	—	3.13/3.29 2.46/2.60	
Output Pad Transition Times, rise/fall (Low Drive. ipp_dse=001)	tr, tf	15 pF Cload, slow slew rate 15 pF Cload, fast slew rate	—	—	5.14/5.57 4.77/5.15	
Input Transition Times[1]	trm	—	—	—	25	ns

[1] Hysteresis mode is recommended for inputs with transition times greater than 25 ns.

4.7.2 DDR I/O AC Parameters

The LPDDR2 interface mode fully complies with JESD209-2B LPDDR2 JEDEC standard release June, 2009. The DDR3/DDR3L interface mode fully complies with JESD79-3D DDR3 JEDEC standard release April, 2008.

Table 31 shows the AC parameters for DDR I/O operating in LPDDR2 mode.

Table 31. DDR I/O LPDDR2 Mode AC Parameters[1]

Parameter	Symbol	Test Condition	Min	Max	Unit
AC input logic high	Vih(ac)	—	Vref + 0.22	OVDD	V
AC input logic low	Vil(ac)	—	0	Vref - 0.22	V
AC differential input high voltage[2]	Vidh(ac)	—	0.44	—	V
AC differential input low voltage	Vidl(ac)	—	—	0.44	V
Input AC differential cross point voltage[3]	Vix(ac)	Relative to Vref	-0.12	0.12	V
Over/undershoot peak	Vpeak	—	—	0.35	V
Over/undershoot area (above OVDD or below OVSS)	Varea	400 MHz	—	0.3	V-ns
Single output slew rate, measured between Vol(ac) and Voh(ac)	tsr	50 Ω to Vref. 5 pF load. Drive impedance = 40 Ω ± 30%	1.5	3.5	V/ns
		50 Ω to Vref. 5pF load.Drive impedance = 60 Ω ± 30%	1	2.5	
Skew between pad rise/fall asymmetry + skew caused by SSN	t_{SKD}	clk = 400 MHz	—	0.1	ns

[1] Note that the JEDEC LPDDR2 specification (JESD209_2B) supersedes any specification in this document.

4.9.3.4 Examples of EIM Synchronous Accesses

Table 43. EIM Bus Timing Parameters [1]

ID	Parameter	BCD = 0		BCD = 1		BCD = 2		BCD = 3	
		Min	Max	Min	Max	Min	Max	Min	Max
WE1	BCLK Cycle time[2]	t	—	2 x t		3 x t	—	4 x t	—
WE2	BCLK Low Level Width	0.4 x t	—	0.8 x t		1.2 x t	—	1.6 x t	—
WE3	BCLK High Level Width	0.4 x t	—	0.8 x t		1.2 x t	—	1.6 x t	—
WE4	Clock rise to address valid[3]	-0.5 x t - 1.25	-0.5 x t + 1.75	-t - 1.25	-t + 1.75	-1.5 x t - 1.25	-1.5 x t +1.75	-2 x t - 1.25	-2 x t + 1.75
WE5	Clock rise to address invalid	0.5 x t - 1.25	0.5 x t + 1.75	t - 1.25	t + 1.75	1.5 x t - 1.25	1.5 x t +1.75	2 x t - 1.25	2 x t + 1.75
WE6	Clock rise to CSx_B valid	-0.5 x t - 1.25	-0.5 x t + 1.75	-t - 1.25	- t + 1.75	-1.5 x t - 1.25	-1.5 x t +1.75	-2 x t - 1.25	-2 x t + 1.75
WE7	Clock rise to CSx_B invalid	0.5 x t - 1.25	0.5 x t + 1.75	t - 1.25	t + 1.75	1.5 x t - 1.25	1.5 x t +1.75	2 x t - 1.25	2 x t + 1.75
WE8	Clock rise to WE_B Valid	-0.5 x t - 1.25	-0.5 x t + 1.75	-t - 1.25	- t + 1.75	-1.5 x t - 1.25	-1.5 x t +1.75	-2 x t - 1.25	-2 x t + 1.75
WE9	Clock rise to WE_B Invalid	0.5 x t - 1.25	0.5 x t + 1.75	t - 1.25	t + 1.75	1.5 x t - 1.25	1.5 x t +1.75	2 x t - 1.25	2 x t + 1.75
WE10	Clock rise to OE_B Valid	-0.5 x t - 1.25	-0.5 x t + 1.75	-t - 1.25	- t + 1.75	-1.5 x t - 1.25	-1.5 x t +1.75	-2 x t - 1.25	-2 x t + 1.75
WE11	Clock rise to OE_B Invalid	0.5 x t - 1.25	0.5 x t + 1.75	t - 1.25	t + 1.75	1.5 x t - 1.25	1.5 x t +1.75	2 x t - 1.25	2 x t + 1.75
WE12	Clock rise to BEy_B Valid	-0.5 x t - 1.25	-0.5 x t + 1.75	-t - 1.25	- t + 1.75	-1.5 x t - 1.25	-1.5 x t +1.75	-2 x t - 1.25	-2 x t + 1.75
WE13	Clock rise to BEy_B Invalid	0.5 x t - 1.25	0.5 x t + 1.75	t - 1.25	t + 1.75	1.5 x t - 1.25	1.5 x t +1.75	2 x t - 1.25	2 x t + 1.75
WE14	Clock rise to ADV_B Valid	-0.5 x t - 1.25	-0.5 x t + 1.75	-t - 1.25	- t + 1.75	-1.5 x t - 1.25	-1.5 x t +1.75	-2 x t - 1.25	-2 x t + 1.75
WE15	Clock rise to ADV_B Invalid	0.5 x t - 1.25	0.5 x t + 1.75	t - 1.25	t + 1.75	1.5 x t - 1.25	1.5 x t +1.75	2 x t - 1.25	2 x t + 1.75
WE16	Clock rise to Output Data Valid	-0.5 x t - 1.25	-0.5 x t + 1.75	-t - 1.25	- t + 1.75	-1.5 x t - 1.25	-1.5 x t +1.75	-2 x t - 1.25	-2 x t + 1.75
WE17	Clock rise to Output Data Invalid	0.5 x t - 1.25	0.5 x t + 1.75	t - 1.25	t + 1.75	1.5 x t - 1.25	1.5 x t +1.75	2 x t - 1.25	2 x t + 1.75
WE18	Input Data setup time to Clock rise	2	—	4	—	—	—	—	—

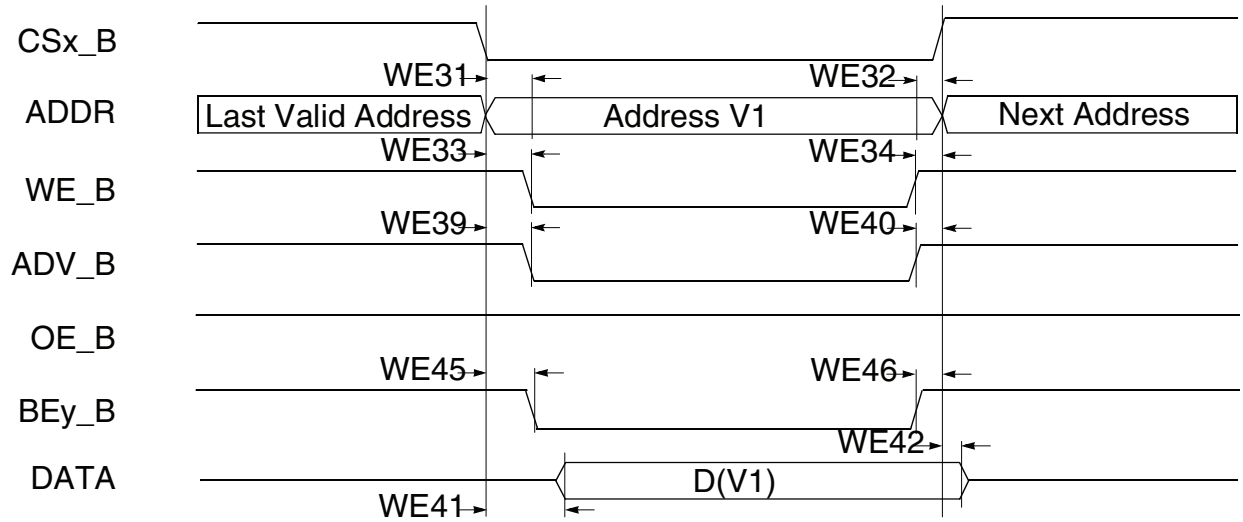


Figure 20. Asynchronous Memory Write Access

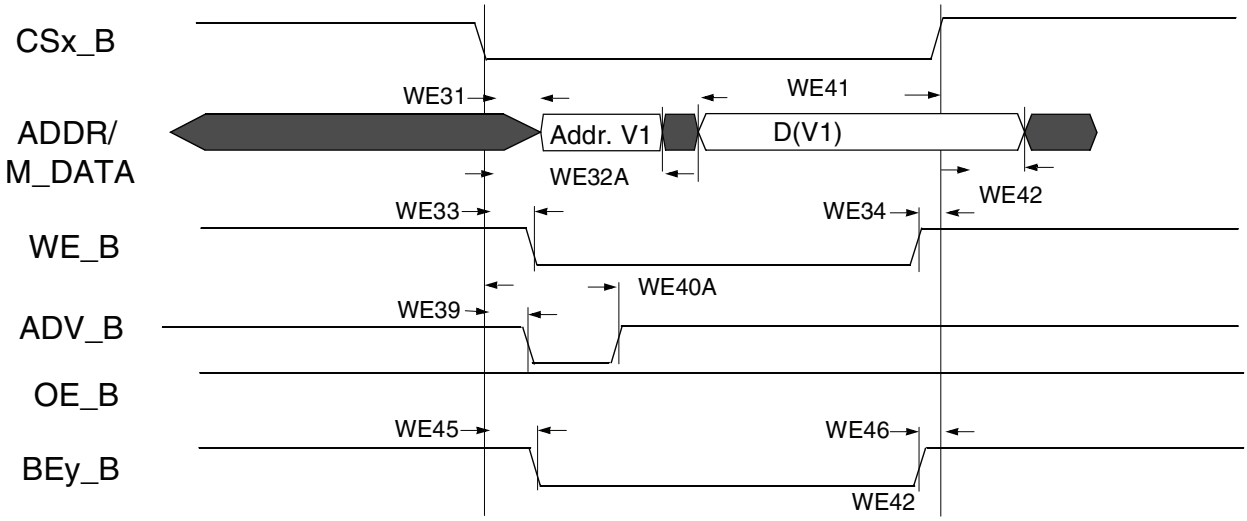


Figure 21. Asynchronous A/D Muxed Write Access

Table 44. EIM Asynchronous Timing Parameters Table Relative Chip Select

Ref No.	Parameter	Determination by Synchronous measured parameters[1]	Min	Max (If 132 MHz is supported by SoC)	Unit
WE31	CSx_B valid to Address Valid	WE4 - WE6 - CSA[2]	—	3 - CSA	ns
WE32	Address Invalid to CSx_B invalid	WE7 - WE5 - CSN[3]	—	3 - CSN	ns
WE32A(muxed A/D	CSx_B valid to Address Invalid	t[4] + WE4 - WE7 + (ADVN[5] + ADVA[6] + 1 - CSA)	-3 + (ADVN + ADVA + 1 - CSA)	—	ns
WE33	CSx_B Valid to WE_B Valid	WE8 - WE6 + (WEA - WCSA)	—	3 + (WEA - WCSA)	ns
WE34	WE_B Invalid to CSx_B Invalid	WE7 - WE9 + (WEN - WCSN)	—	3 - (WEN_WCSN)	ns
WE35	CSx_B Valid to OE_B Valid	WE10 - WE6 + (OEA - RCSA)	—	3 + (OEA - RCSA)	ns
WE35A (muxed A/D)	CSx_B Valid to OE_B Valid	WE10 - WE6 + (OEA + RADVN + RADVA + ADH + 1 - RCSA)	-3 + (OEA + RADVN+RADVA+ ADH+1-RCSA)	3 + (OEA + RADVN+RADVA+AD H+1-RCSA)	ns
WE36	OE_B Invalid to CSx_B Invalid	WE7 - WE11 + (OEN - RCSN)	—	3 - (OEN - RCSN)	ns
WE37	CSx_B Valid to BEy_B Valid (Read access)	WE12 - WE6 + (RBEA - RCSA)	—	3 + (RBEA - RCSA)	ns
WE38	BEy_B Invalid to CSx_B Invalid (Read access)	WE7 - WE13 + (RBEN - RCSN)	—	3 - (RBEN- RCSN)	ns
WE39	CSx_B Valid to ADV_B Valid	WE14 - WE6 + (ADVA - CSA)	—	3 + (ADVA - CSA)	ns
WE40	ADV_B Invalid to CSx_B Invalid (ADVL is asserted)	WE7 - WE15 - CSN	—	3 - CSN	ns
WE40A (muxed A/D)	CSx_B Valid to ADV_B Invalid	WE14 - WE6 + (ADVN + ADVA + 1 - CSA)	-3 + (ADVN + ADVA + 1 - CSA)	3 + (ADVN + ADVA + 1 - CSA)	ns
WE41	CSx_B Valid to Output Data Valid	WE16 - WE6 - WCSA	—	3 - WCSA	ns
WE41A (muxed A/D)	CSx_B Valid to Output Data Valid	WE16 - WE6 + (WADVN + WADVA + ADH + 1 - WCSA)	—	3 + (WADVN + WADVA + ADH + 1 - WCSA)	ns
WE42	Output Data Invalid to CSx_B Invalid	WE17 - WE7 - CSN	—	3 - CSN	ns
MAXCO	Output max. delay from internal driving ADDR/control FFs to chip outputs.	10	—	—	ns
MAXCS O	Output max. delay from CSx internal driving FFs to CSx out.	10	—	—	
MAXDI	DATA MAXIMUM delay from chip input data to its internal FF	5	—	—	

1 All measurements are in reference to Vref level.

2 Measurements were done using balanced load and 25 Ω resistor from outputs to VDD_REF.

Figure 25shows the DDR3/DDR3L write timing parameters. The timing parameters for this diagram appear in Table 46.

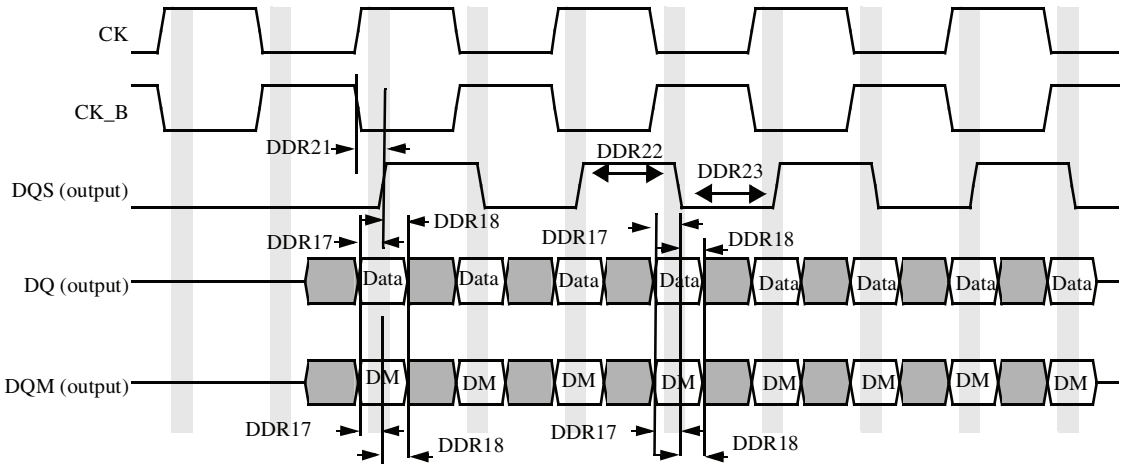


Figure 25. DDR3/DDR3L Write Cycle

Table 46. DDR3/DDR3L Write Cycle

ID	Parameter	Symbol	CK = 400 MHz		Unit
			Min	Max	
DDR17	DQ and DQM setup time to DQS (differential strobe)	t_{DS}	420	—	ps
DDR18	DQ and DQM hold time to DQS (differential strobe)	t_{DH}	345	—	ps
DDR21	DQS latching rising transitions to associated clock edges	t_{DQSS}	-0.25	+0.25	tCK
DDR22	DQS high level width	t_{DQSH}	0.45	0.55	tCK
DDR23	DQS low level width	t_{DQSL}	0.45	0.55	tCK

1 To receive the reported setup and hold values, write calibration should be performed in order to locate the DQS in the middle of DQ window.

2 All measurements are in reference to Vref level.

3 Measurements were done using balanced load and 25 Ω resistor from outputs to VDD_REF.

4.10.3.2 Read and Write Timing

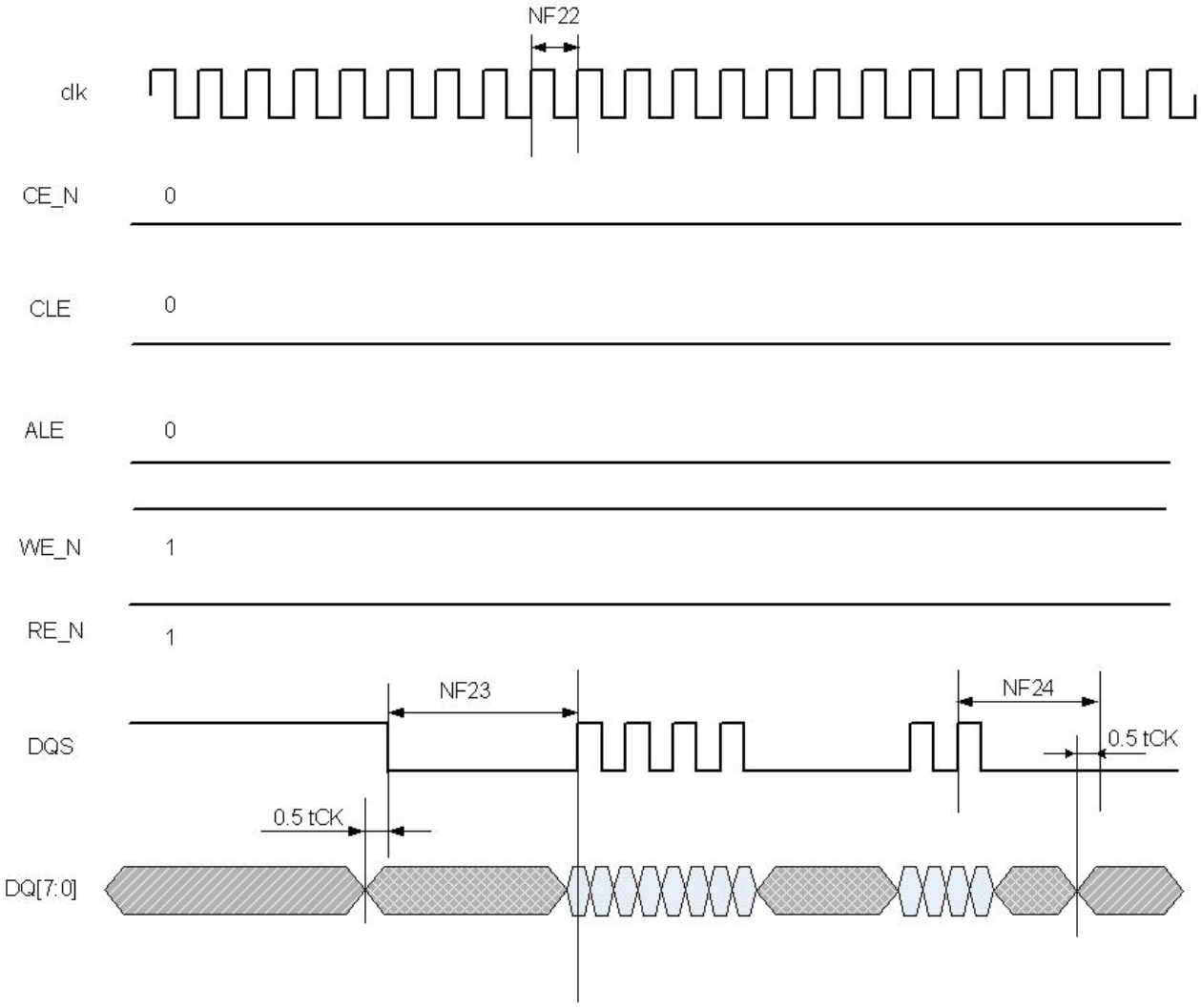


Figure 38. Samsung Toggle Mode Data Write Timing

4.11.2.1 ECSPI Master Mode Timing

Figure 40 depicts the timing of ECSPI in master mode. Table 54 lists the ECSPI master mode timing characteristics.

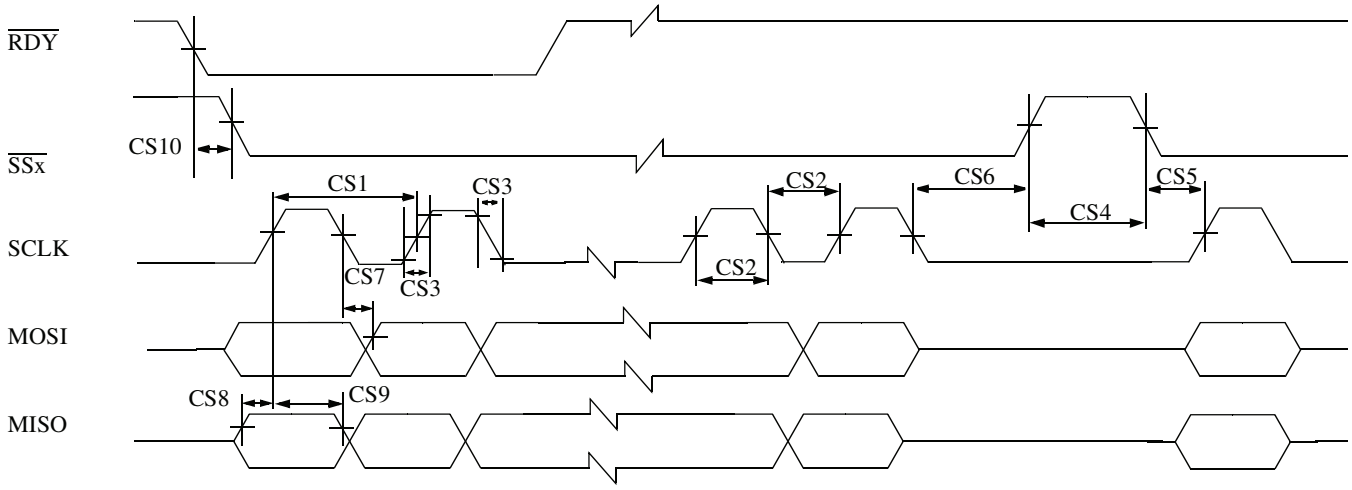


Figure 40. ECSPI Master Mode Timing Diagram

Table 54. ECSPI Master Mode Timing Parameters

ID	Parameter	Symbol	Min	Max	Unit
CS1	SCLK Cycle Time–Read SCLK Cycle Time–Write	t_{clk}	43 15	—	ns
CS2	SCLK High or Low Time–Read SCLK High or Low Time–Write	t_{SW}	21.5 7	—	ns
CS3	SCLK Rise or Fall[1]	$t_{RISE/FALL}$	—	—	ns
CS4	SSx pulse width	t_{CSLH}	Half SCLK period	—	ns
CS5	SSx Lead Time (CS setup time)	t_{SCS}	Half SCLK period - 4	—	ns
CS6	SSx Lag Time (CS hold time)	t_{HCS}	Half SCLK period - 2	—	ns
CS7	MOSI Propagation Delay (C_{LOAD} = 20 pF)	t_{PDmosi}	-1	1	ns
CS8	MISO Setup Time	t_{Smiso}	18	—	ns
CS9	MISO Hold Time	t_{Hmiso}	0	—	ns
CS10	RDY to SSx Time[2]	t_{SDRY}	5	—	ns

1 See specific I/O AC parameters Section 4.7, “I/O AC Parameters.”

2 SPI_RDY is sampled internally by ipg_clk and is asynchronous to all other CSPI signals.

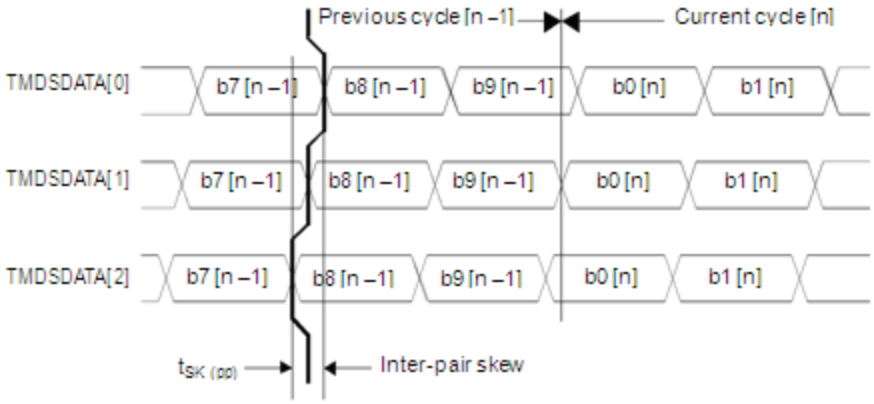


Figure 61. Inter-Pair Skew Definition

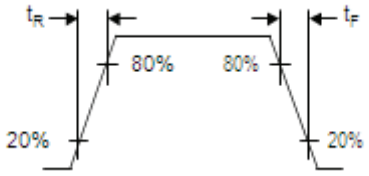


Figure 62. TMDS Output Signals Rise and Fall Time Definition

Table 67. Switching Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
TMDS Drivers Specifications						
—	Maximum serial data rate	—	—	—	3.4	Gbps
$F_{TMDSCLK}$	TMDSCLK frequency	On TMDSCLKP/N outputs	25	—	340	MHz
$P_{TMDSCLK}$	TMDSCLK period	RL = 50 Ω See Figure 58.	2.94	—	40	ns
t_{CDC}	TMDSCLK duty cycle	$t_{CDC} = t_{CPH} / P_{TMDSCLK}$ RL = 50 Ω See Figure 58.	40	50	60	%
t_{CPH}	TMDSCLK high time	RL = 50 Ω See Figure 58.	4	5	6	UI[1]
t_{CPL}	TMDSCLK low time	RL = 50 Ω See Figure 58.	4	5	6	UI[1]
—	TMDSCLK jitter[2]	RL = 50 Ω	—	—	0.25	UI[1]
$t_{SK(p)}$	Intra-pair (pulse) skew	RL = 50 Ω See Figure 60.	—	—	0.15	UI[1]

Table 68. I²C Module Timing Parameters (continued)

ID	Parameter	Standard Mode		Fast Mode		Unit
		Min	Max	Min	Max	
IC8	Data set-up time	250	—	100[3]	—	ns
IC9	Bus free time between a STOP and START condition	4.7	—	1.3	—	µs
IC10	Rise time of both I2DAT and I2CLK signals	—	1000	$20 + 0.1C_b$[4]	300	ns
IC11	Fall time of both I2DAT and I2CLK signals	—	300	$20 + 0.1C_b$[4]	300	ns
IC12	Capacitive load for each bus line (C_b)	—	400	—	400	pF

1 A device must internally provide a hold time of at least 300 ns for I2DAT signal in order to bridge the undefined region of the falling edge of I2CLK.

2 The maximum hold time has only to be met if the device does not stretch the LOW period (ID no IC5) of the I2CLK signal.

3 A Fast-mode I²C-bus device can be used in a Standard-mode I²C-bus system, but the requirement of Set-up time (ID No IC7) of 250 ns must be met. This automatically is the case if the device does not stretch the LOW period of the I2CLK signal. If such a device does stretch the LOW period of the I2CLK signal, it must output the next data bit to the I2DAT line max_rise_time (IC9) + data_setup_time (IC7) = 1000 + 250 = 1250 ns (according to the Standard-mode I²C-bus specification) before the I2CLK line is released.

4 C_b = total capacitance of one bus line in pF.

4.11.10 Image Processing Unit (IPU) Module Parameters

The purpose of the IPU is to provide comprehensive support for the flow of data from an image sensor and/or to a display device. This support covers all aspects of these activities:

- Connectivity to relevant devices—cameras, displays, graphics accelerators, and TV encoders.
- Related image processing and manipulation: sensor image signal processing, display processing, image conversions, and other related functions.
- Synchronization and control capabilities, such as avoidance of tearing artifacts.

Table 72 shows timing characteristics of signals presented in Figure 68 and Figure 69.

Table 72. Synchronous Display Interface Timing Characteristics (Pixel Level)

ID	Parameter	Symbol	Value	Description	Unit
IP5	Display interface clock period	Tdicp	([1])	Display interface clock. IPP_DISP_CLK	ns
IP6	Display pixel clock period	Tdpcp	DISP_CLK_PER_PIXEL × Tdicp	Time of translation of one pixel to display, DISP_CLK_PER_PIXEL—number of pixel components in one pixel (1.n). The DISP_CLK_PER_PIXEL is virtual parameter to define Display pixel clock period. The DISP_CLK_PER_PIXEL is received by DC/DI one access division to **n** components.	ns
IP7	Screen width time	Tsw	(SCREEN_WIDTH) × Tdicp	SCREEN_WIDTH—screen width in, interface clocks. horizontal blanking included. The SCREEN_WIDTH should be built by suitable DI's counter[2].	ns
IP8	HSYNC width time	Thsw	(HSYNC_WIDTH)	HSYNC_WIDTH—Hsync width in DI_CLK with 0.5 DI_CLK resolution. Defined by DI's counter.	ns
IP9	Horizontal blank interval 1	Thbi1	BGXP × Tdicp	BGXP—width of a horizontal blanking before a first active data in a line (in interface clocks). The BGXP should be built by suitable DI's counter.	ns
IP10	Horizontal blank interval 2	Thbi2	(SCREEN_WIDTH - BGXP - FW) × Tdicp	Width a horizontal blanking after a last active data in a line (in interface clocks) FW—with of active line in interface clocks. The FW should be built by suitable DI's counter.	ns
IP12	Screen height	Tsh	(SCREEN_HEIGHT) × Tsw	SCREEN_HEIGHT— screen height in lines with blanking. The SCREEN_HEIGHT is a distance between 2 VSYNCs. The SCREEN_HEIGHT should be built by suitable DI's counter.	ns
IP13	VSYNC width	Tvsw	VSYNC_WIDTH	VSYNC_WIDTH—Vsync width in DI_CLK with 0.5 DI_CLK resolution. Defined by DI's counter	ns
IP14	Vertical blank interval 1	Tvbi1	BGYP × Tsw	BGYP—width of first Vertical blanking interval in line. The BGYP should be built by suitable DI's counter.	ns
IP15	Vertical blank interval 2	Tvbi2	(SCREEN_HEIGHT - BGYP - FH) × Tsw	Width of second Vertical blanking interval in line. The FH should be built by suitable DI's counter.	ns

Table 72. Synchronous Display Interface Timing Characteristics (Pixel Level) (continued)

ID	Parameter	Symbol	Value	Description	Unit
IP5o	Offset of IPP_DISP_CLK	Todicp	DISP_CLK_OFFSET × Tdiclk	DISP_CLK_OFFSET—offset of IPP_DISP_CLK edges from local start point, in DI_CLK×2 (0.5 DI_CLK Resolution). Defined by DISP_CLK counter	ns
IP13o	Offset of VSYNC	Tovs	VSYNC_OFFSET × Tdiclk	VSYNC_OFFSET—offset of Vsync edges from a local start point, when a Vsync should be active, in DI_CLK×2 (0.5 DI_CLK Resolution). The VSYNC_OFFSET should be built by suitable DI's counter.	ns
IP8o	Offset of HSYNC	Tohs	HSYNC_OFFSET × Tdiclk	HSYNC_OFFSET—offset of Hsync edges from a local start point, when a Hsync should be active, in DI_CLK×2 (0.5 DI_CLK Resolution). The HSYNC_OFFSET should be built by suitable DI's counter.	ns
IP9o	Offset of DRDY	Todrdy	DRDY_OFFSET × Tdiclk	DRDY_OFFSET—offset of DRDY edges from a suitable local start point, when a corresponding data has been set on the bus, in DI_CLK×2 (0.5 DI_CLK Resolution). The DRDY_OFFSET should be built by suitable DI's counter.	ns

[1] Display interface clock period immediate value.

$$Tdicp = \begin{cases} T_{diclk} \times \dfrac{DISP\_CLK\_PERIOD}{DI\_CLK\_PERIOD}, & \text{for integer } \dfrac{DISP\_CLK\_PERIOD}{DI\_CLK\_PERIOD} \\ T_{diclk}\left(floor\left[\dfrac{DISP\_CLK\_PERIOD}{DI\_CLK\_PERIOD}\right] + 0.5 \pm 0.5\right), & \text{for fractional } \dfrac{DISP\_CLK\_PERIOD}{DI\_CLK\_PERIOD} \end{cases}$$

DISP_CLK_PERIOD—number of DI_CLK per one Tdicp. Resolution 1/16 of DI_CLK.
DI_CLK_PERIOD—relation of between programing clock frequency and current system clock frequency
Display interface clock period average value.

$$\overline{T}dicp = T_{diclk} \times \frac{DISP\_CLK\_PERIOD}{DI\_CLK\_PERIOD}$$

[2] DI's counter can define offset, period and UP/DOWN characteristic of output signal according to programed parameters of the counter. Same of parameters in the table are not defined by DI's registers directly (by name), but can be generated by corresponding DI's counter. The SCREEN_WIDTH is an input value for DI's HSYNC generation counter. The distance between HSYNCs is a SCREEN_WIDTH.

The maximal accuracy of UP/DOWN edge of controls is:

$$Accuracy = (0.5 \times T_{diclk}) \pm 0.62ns$$

Table 79. MediaLB 6-Pin Interface Electrical DC Specifications (continued)

Parameter	Symbol	Test Conditions	Min	Max	Unit
Differential clock input: • logic low steady-state • logic high steady-state • hysteresis	 V_{ILC} V_{IHC} V_{HSC}	See Note[4]	 50 -25	 -50 25	 mV mV mV
Differential signal/data input: • logic low steady-state • logic high steady-state	 V_{ILS} V_{IHS}	—	 50	 -50 	 mV mV
Signal-ended input voltage (steady-state): • MLBSP, MLBDP • MLBSN, MLBDN	 V_{IN+} V_{IN-}	—	 0.5 0.5	 2.0 2.0	 V V

1 The signal-ended output voltage of a driver is defined as V_{O+} on MLBCP, MLBSP, and MLBDP. The signal-ended output voltage of a driver is defined as V_{O-} on MLBCN, MLBSN, and MLBDN.

2 Variations in the common-mode voltage can occur between logic states (for example, during state transitions) as a result of differences in the transition rate of V_{O+} and V_{O-}.

3 Short circuit current is applicable when V_{O+} and V_{O-} are shorted together and/or shorted to ground.

4 The logic state of the receiver is undefined when -50 mV < V_{ID} < 50 mV.

4.11.14.2 MediaLB (MLB) Controller AC Timing Electrical Specifications

This section describes the timing electrical information of the MediaLB module. Figure 86 show the timing of MediaLB 3-pin interface, and Table 80 and Table 81 lists the MediaLB 3-pin interface timing characteristics.

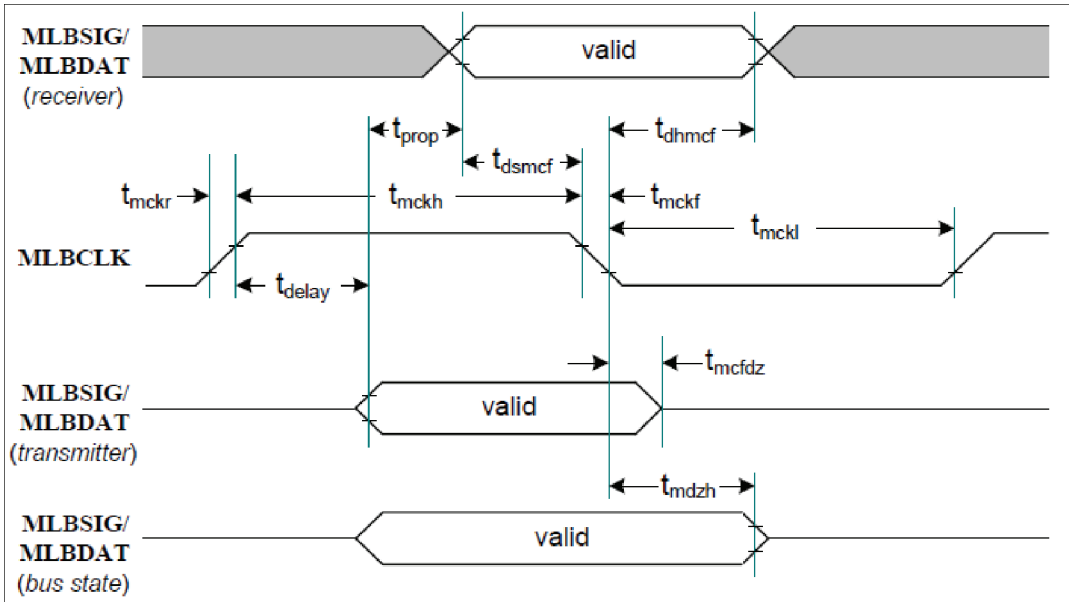


Figure 86. MediaLB 3-Pin Timing

Ground = 0.0 V; Load Capacitance = 60 pF; MediaLB speed = 256/512 Fs; Fs = 48 kHz; all timing parameters specified from the valid voltage threshold as listed below; unless otherwise noted.

Table 81. MLB 1024 Fs Timing Parameters (continued)

Parameter	Symbol	Min	Max	Unit	Comment
MLBSIG/MLBDAT output high impedance from MLBCLK low	t_{mcfdz}	0	t_{mckl}	ns	[3]
Bus Hold from MLBCLK low	t_{mdzh}	2	—	ns	—
MLBSIG/MLBDAT output valid from transition of MLBCLK (low to high)	t_{delay}	—	7	ns	—

[1] The controller can shut off MLBCLK to place MediaLB in a low-power state. Depending on the time the clock is shut off, a runt pulse can occur on MLBCLK.

[2] MLBCLK low/high time includes the pulse width variation.

[3] The MediaLB driver can release the MLBDAT/MLBSIG line as soon as MLBCLK is low; however, the logic state of the final driven bit on the line must remain on the bus for t_{mdzh}. Therefore, coupling must be minimized while meeting the maximum load capacitance listed.

Table 82 lists the MediaLB 6-pin interface timing characteristics, and Figure 87 shows the MLB 6-pin delay, setup, and hold times.

Table 82. MLB 6-Pin Interface Timing Parameters

Parameter	Symbol	Min	Max	Unit	Comment
Cycle-to-cycle system jitter	t_{jitter}	—	600	ps	—
Transmitter MLBSP/N (MLBDP/N) output valid from transition of MLBCP/N (low-to-high)[1]	t_{delay}	0.6	1.3	ns	
Disable turnaround time from transition of MLBCP/N (low-to-high)	t_{phz}	0.6	3.5	ns	
Enable turnaround time from transition of MLBCP/N (low-to-high)	t_{plz}	0.6	5.6	ns	
MLBSP/N (MLBDP/N) valid to transition of MLBCP/N (low-to-high)	t_{su}	0.05	—	ns	
MLBSP/N (MLBDP/N) hold from transition of MLBCP/N (low-to-high)[2]	t_{hd}	0.6			

[1] t_{delay}, t_{phz}, t_{plz}, t_{su}, and t_{hd} may also be referenced from a low-to-high transition of the recovered clock for 2:1 and 4:1 recovered-to-external clock ratios.

[2] The transmitting device must ensure valid data on MLBSP/N (MLBDP/N) for at least $t_{hd(min)}$ following the rising edge of MLBCP/N; receivers must latch MLBSP/N (MLBDP/N) data within $t_{hd(min)}$ of the rising edge of MLBCP/N.

4.11.19.2 SSI Receiver Timing with Internal Clock

Figure 96 depicts the SSI receiver internal clock timing and Table 88 lists the timing parameters for the receiver timing with the internal clock.

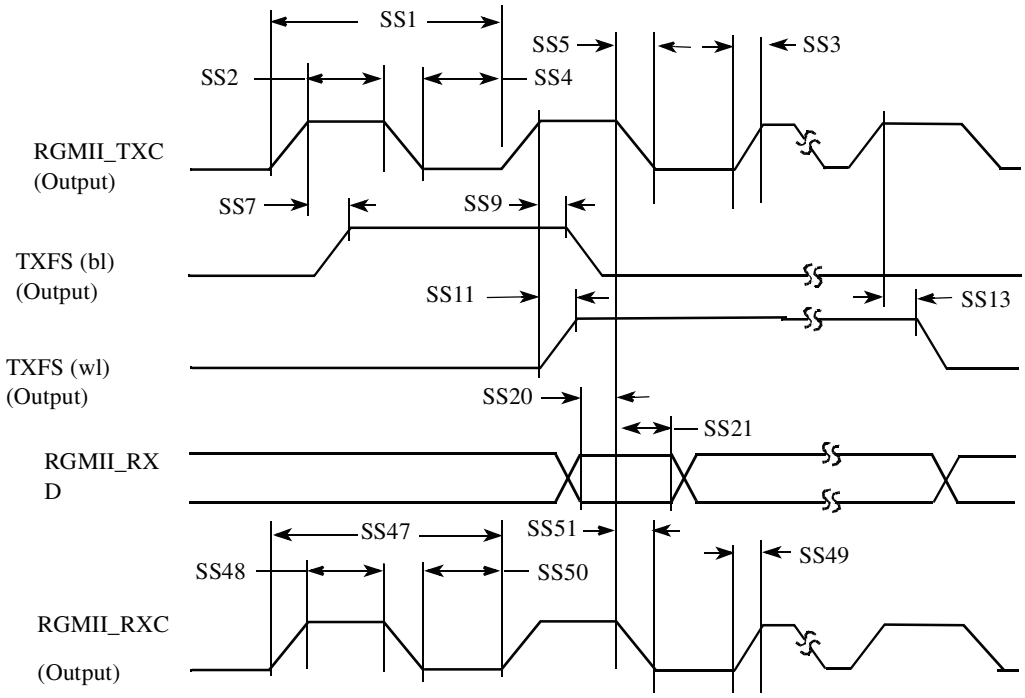


Figure 96. SSI Receiver Internal Clock Timing Diagram

Table 88. SSI Receiver Timing with Internal Clock

ID	Parameter	Min	Max	Unit
Internal Clock Operation				
SS1	(Tx/Rx) CK clock period	81.4	—	ns
SS2	(Tx/Rx) CK clock high period	36.0	—	ns
SS3	(Tx/Rx) CK clock rise time	—	6.0	ns
SS4	(Tx/Rx) CK clock low period	36.0	—	ns
SS5	(Tx/Rx) CK clock fall time	—	6.0	ns
SS7	(Rx) CK high to FS (bl) high	—	15.0	ns
SS9	(Rx) CK high to FS (bl) low	—	15.0	ns
SS11	(Rx) CK high to FS (wl) high	—	15.0	ns
SS13	(Rx) CK high to FS (wl) low	—	15.0	ns
SS20	SRXD setup time before (Rx) CK low	10.0	—	ns
SS21	SRXD hold time after (Rx) CK low	0.0	—	ns
Oversampling Clock Operation				

Table 100. 21 x 21 mm Supplies Contact Assignments (continued)

Supply Rail Name	Ball(s) Position(s)	Remark
PCIE_REXT	A2	
PCIE_VP	H7	
PCIE_VPH	G7	PCI PHY supply
PCIE_VPTX	G8	PCI PHY supply
VDD_SNVS_CAP	G9	Secondary supply for the SNVS (internal regulator output—requires capacitor if internal regulator is used)
VDD_SNVS_IN	G11	Primary supply for the SNVS regulator
VDDARM_CAP	H11, H13, J11, J13, K11, K13, L11, L13, M11, M13, N11, N13, P11, P13, R11, R13	Secondary supply for core (internal regulator output—requires capacitor if internal regulator is used)
VDDARM_IN	H14, J14, K9, K14, L9, L14, M9, M14, N9, N14, P9, P14, R9, R14, T9, U9	Primary supply for the ARM core's regulator
VDDHIGH_CAP	H10, J10	Secondary supply for the 2.5 V domain (internal regulator output—requires capacitor if internal regulator is used)
VDDHIGH_IN	H9, J9	Primary supply for the 2.5 V regulator
VDDPU_CAP	H17, J17, K17, L17, M17, N17, P17	Secondary supply for VPU and GPUs (internal regulator output—requires capacitor if internal regulator is used)
VDDSOC_CAP	R10, T10, T13, T14, U10, U13, U14	Secondary supply for SoC and PU regulators (internal regulator output—requires capacitor if internal regulator is used)
VDDSOC_IN	H16, J16, K16, L16, M16, N16, P16, R16, T16, U16	Primary supply for SoC and PU regulators
VDDUSB_CAP	F9	Secondary supply for the 3 V Domain (internal regulator output—requires capacitor if internal regulator is used)
USB_H1_VBUS	D10	Primary supply for the 3 V regulator
USB_OTG_VBUS	E9	Primary supply for the 3 V regulator
HDMI_DDCCEC	K2	Analog Ground(Ground reference for the Hot Plug Detect signal)
FA_ANA	A5	
GPANAIO	C8	
VDD_FA	B5	
ZQPAD	AE17	
NC	C14	
NC	G12	

Table 102. 21 x 21 mm, 0.8 mm Pitch Ball Map (continued)

R	P	N	M	L	K	J	H
GPIO_17	CSI0_PIXCLK	CSI0_DAT4	CSI0_DAT10	CSI0_DAT13	HDMI_HPD	HDMI_REF	DSI_D1P
GPIO_16	CSI0_DAT5	CSI0_VSYNC	CSI0_DAT12	GND	HDMI_DDCCEC	GND	DSI_D1M
GPIO_7	CSI0_DATA_EN	CSI0_DAT7	CSI0_DAT11	CSI0_DAT17	HDMI_D2M	HDMI_D1M	DSI_CLK0M
GPIO_5	CSI0_MCLK	CSI0_DAT6	CSI0_DAT14	CSI0_DAT16	HDMI_D2P	HDMI_D1P	DSI_CLK0P
GPIO_8	GPIO_19	CSI0_DAT9	CSI0_DAT15	GND	HDMI_D0M	HDMI_CLKM	JTAG_TCK
GPIO_4	GPIO_18	CSI0_DAT8	CSI0_DAT18	CSI0_DAT19	HDMI_D0P	HDMI_CLKP	JTAG_MOD
GPIO_3	NVCC_GPIO	NVCC_CSI	HDMI_VPH	HDMI_VP	NVCC_MIPI	NVCC_JTAG	PCIE_VP
GND	GND	GND	GND	GND	GND	GND	GND
VDDARM_IN	VDDARM_IN	VDDARM_IN	VDDARM_IN	VDDARM_IN	VDDARM_IN	VDDHIGH_IN	VDDHIGH_IN
VDDSOC_CAP	GND	GND	GND	GND	GND	VDDHIGH_CAP	VDDHIGH_CAP
VDDARM_CAP	VDDARM_CAP	VDDARM_CAP	VDDARM_CAP	VDDARM_CAP	VDDARM_CAP	VDDARM_CAP	VDDARM_CAP
GND	GND	NC	GND	GND	GND	GND	GND
VDDARM_CAP	VDDARM_CAP	VDDARM_CAP	VDDARM_CAP	VDDARM_CAP	VDDARM_CAP	VDDARM_CAP	VDDARM_CAP
VDDARM_IN	VDDARM_IN	VDDARM_IN	VDDARM_IN	VDDARM_IN	VDDARM_IN	VDDARM_IN	VDDARM_IN
GND	GND	GND	GND	GND	GND	GND	GND
VDDSOC_IN	VDDSOC_IN	VDDSOC_IN	VDDSOC_IN	VDDSOC_IN	VDDSOC_IN	VDDSOC_IN	VDDSOC_IN
GND	VDDPU_CAP	VDDPU_CAP	VDDPU_CAP	VDDPU_CAP	VDDPU_CAP	VDDPU_CAP	VDDPU_CAP
NVCC_DRAM	GND	GND	GND	GND	GND	GND	GND
NVCC_ENET	NVCC_LCD	DI0_DISP_CLK	NVCC_EIM	NVCC_EIM	NVCC_EIM	EIM_D29	EIM_A25
DISP0_DAT13	DISP0_DAT4	DI0_PIN3	EIM_DA11	EIM_DA0	EIM_RW	EIM_D30	EIM_D21
DISP0_DAT10	DISP0_DAT3	DI0_PIN15	EIM_DA9	EIM_DA2	EIM_EB0	EIM_A23	EIM_D31
DISP0_DAT8	DISP0_DAT1	EIM_BCLK	EIM_DA10	EIM_DA4	EIM_LBA	EIM_A18	EIM_A20
DISP0_DAT6	DISP0_DAT2	EIM_DA14	EIM_DA13	EIM_DA5	EIM_EB1	EIM_CS1	EIM_A21
DISP0_DAT7	DISP0_DAT0	EIM_DA15	EIM_DA12	EIM_DA8	EIM_DA3	EIM_OE	EIM_CS0
DISP0_DAT5	DI0_PIN4	DI0_PIN2	EIM_WAIT	EIM_DA7	EIM_DA6	EIM_DA1	EIM_A16
R	P	N	M	L	K	J	H